

**Features**

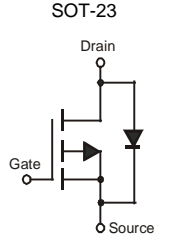
- Low  $R_{DS(ON)}$ :
  - 72 m $\Omega$  @  $V_{GS} = -4.5V$
  - 108 m $\Omega$  @  $V_{GS} = -2.7V$
  - 123 m $\Omega$  @  $V_{GS} = -2.5V$
- Low Input/Output Leakage
- **Lead Free By Design/RoHS Compliant (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **"Green" Device (Note 4)**

**Mechanical Data**

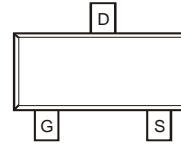
- Case: SOT-23
- Case Material - Molded Plastic, "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish - Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram Below
- Marking Information: See Page 4
- Ordering Information: See page 4
- Weight: 0.008 grams (approximate)



TOP VIEW



Internal Schematic



TOP VIEW

**Maximum Ratings** @ $T_A = 25^\circ C$  unless otherwise specified

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	-20	V
Gate-Source Voltage	$V_{GSS}$	$\pm 12$	V
Drain Current (Note 1) Continuous	$I_D$	-3.0 -2.4	A
		$T_A = 25^\circ C$ $T_A = 70^\circ C$	
Pulsed Drain Current (Note 2)	$I_{DM}$	-15	A
Body-Diode Continuous Current (Note 1)	$I_S$	2.0	A

**Thermal Characteristics**

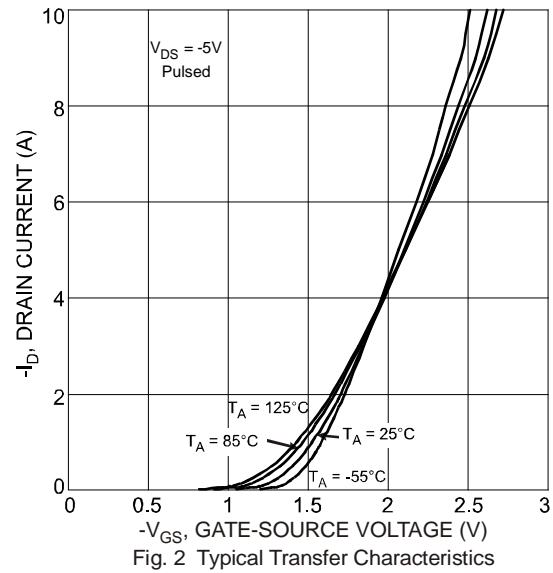
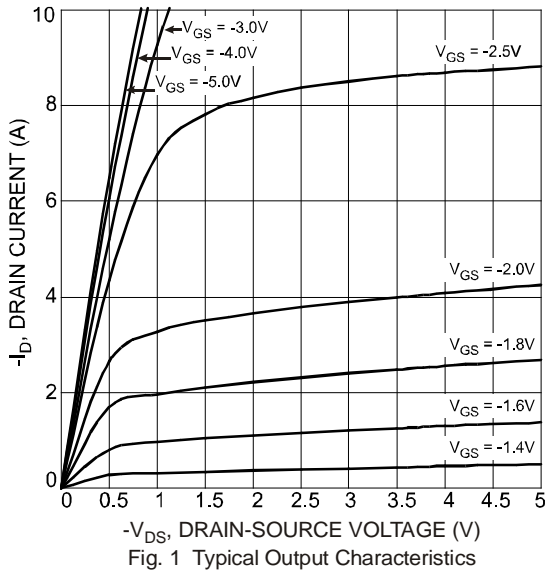
Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	$P_D$	1.4	W
Thermal Resistance, Junction to Ambient (Note 1); Steady-State	$R_{\theta JA}$	90	$^\circ C/W$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ C$

- Notes:
1. Device mounted on 1"x1", FR-4 PC board with 2 oz. Copper and test pulse width  $t \leq 10s$ .
  2. Repetitive Rating, pulse width limited by junction temperature.
  3. No purposefully added lead.
  4. Diodes Inc's "Green" policy can be found on our website at [http://www.diodes.com/products/lead\\_free/index.php](http://www.diodes.com/products/lead_free/index.php).

**Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>STATIC PARAMETERS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	—	—	V	I <sub>D</sub> = -250μA, V <sub>GS</sub> = 0V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-1	μA	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V
Gate-Body Leakage Current	I <sub>GSS</sub>	—	—	±100	nA	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±12V
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.6	—	-1.25	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
On State Drain Current (Note 5)	I <sub>D(ON)</sub>	-15	—	—	A	V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -5V
Static Drain-Source On-Resistance (Note 5)	R <sub>DS(ON)</sub>	—	51	72	mΩ	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3.5A
			87	108		V <sub>GS</sub> = -2.7V, I <sub>D</sub> = -3.0A
			99	123		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -2.6A
Forward Transconductance (Note 5)	g <sub>FS</sub>	—	7.3	—	S	V <sub>DS</sub> = -10V, I <sub>D</sub> = -3.0A
Diode Forward Voltage (Note 5)	V <sub>SD</sub>	—	0.79	-1.26	V	I <sub>S</sub> = -1.7A, V <sub>GS</sub> = 0V
Maximum Body-Diode Continuous Current (Note 1)	I <sub>S</sub>	—	—	1.7	A	—
<b>DYNAMIC PARAMETERS (Note 6)</b>						
Total Gate Charge	Q <sub>g</sub>	—	7.3	—	nC	V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -10V, I <sub>D</sub> = -3.0A
Gate-Source Charge	Q <sub>gs</sub>	—	2.0	—	nC	V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -10V, I <sub>D</sub> = -3.0A
Gate-Drain Charge	Q <sub>gd</sub>	—	1.9	—	nC	V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -10V, I <sub>D</sub> = -3.0A
Turn-On Delay Time	t <sub>D(on)</sub>	—	12	—	ns	V <sub>DS</sub> = -10V, V <sub>GS</sub> = -4.5V, R <sub>L</sub> = 10Ω, R <sub>G</sub> = 6Ω
Turn-On Rise Time	t <sub>r</sub>	—	20	—	ns	
Turn-Off Delay Time	t <sub>D(off)</sub>	—	38	—	ns	
Turn-Off Fall Time	t <sub>f</sub>	—	41	—	ns	
Input Capacitance	C <sub>iss</sub>	—	443	—	pF	V <sub>DS</sub> = -16V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	128	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	101	—	pF	

Notes: 5. Test pulse width t = 300μs.  
6. Guaranteed by design. Not subject to production testing.



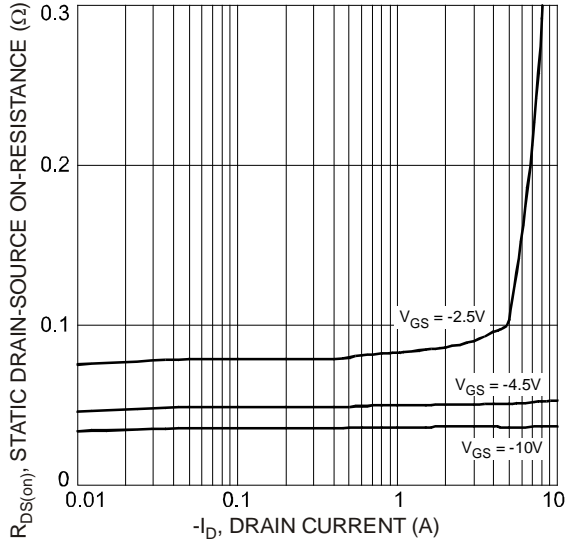


Fig. 3 On-Resistance vs. Drain Current and Gate Voltage

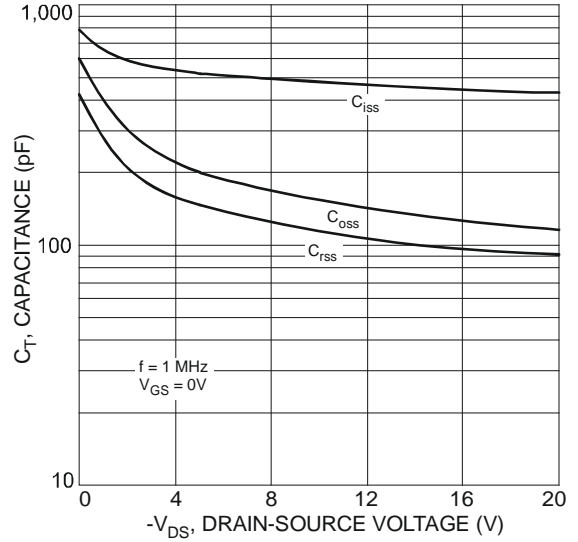


Fig. 4 Typical Total Capacitance

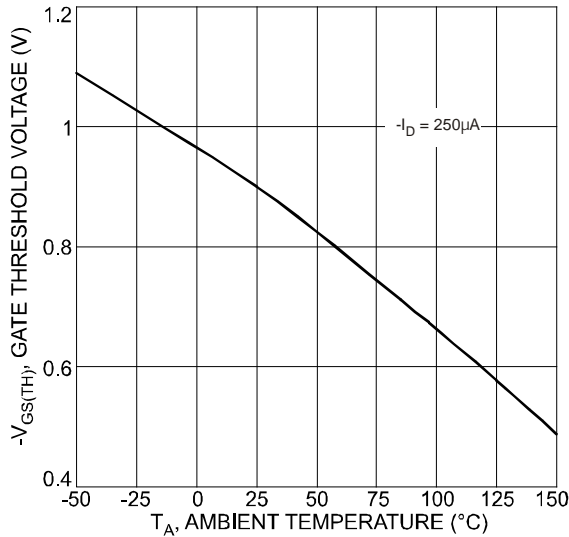


Fig. 5 Gate Threshold Voltage vs. Ambient Temperature

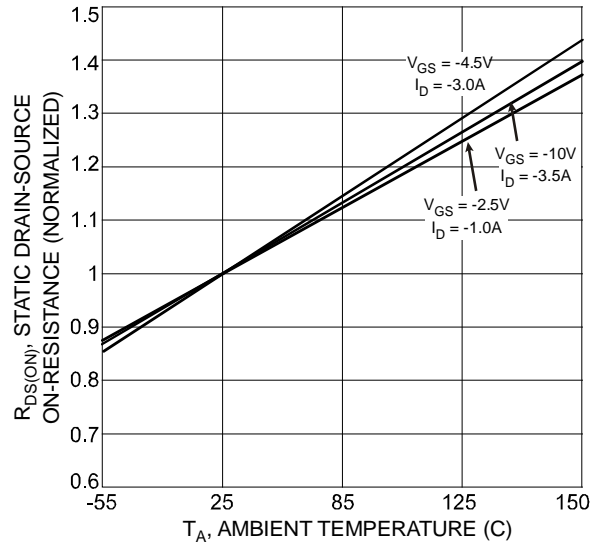


Fig. 6 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

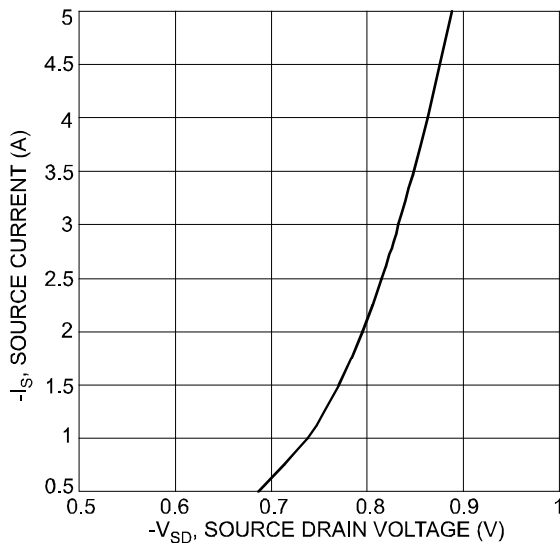


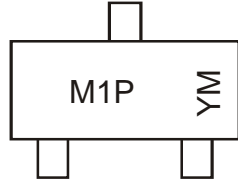
Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

**Ordering Information** (Note 7)

Part Number	Case	Packaging
DMP2123L-7	SOT-23	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

**Marking Information**



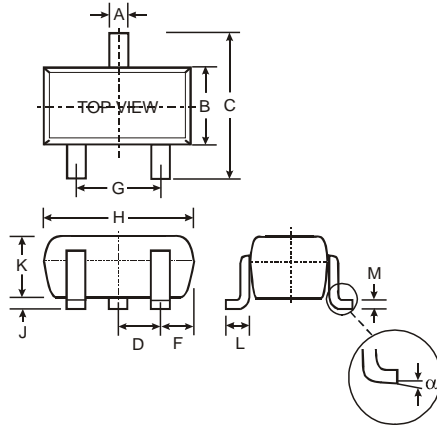
M1P = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year ex: U = 2007  
 M = Month ex: 9 = September

Date Code Key

Year	2007	2008	2009	2010	2011	2012
Code	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

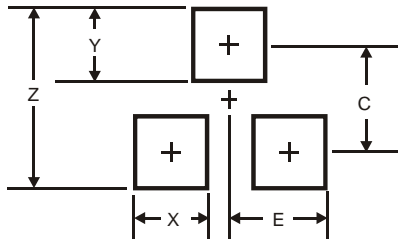
**Package Outline Dimensions**



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
F	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
α	0°	8°

All Dimensions in mm

**Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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